

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

1

Complete If Known	
Application Number	10/075,390
Filing Date	February 15, 2002
First Named Inventor	Kristy A. Campbell
Art Unit	2818
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0505/P505

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
NML	A	5,761,115-	06-02-1998	Kozicki et al.	
NML	B	5,837,564-	11-17-1998	Sandhu et al.	
NML	C	5,896,312-	04-20-1999	Kozicki et al.	
NML	D	5,914,893-	06-22-1999	Kozicki et al.	
NML	E	6,084,796-	07-04-2000	Kozicki et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴ -Number ⁵ -Kind Code ⁶ (if known)				

*Applicant's unique citation designation number (optional). ²See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
NML	F	P. Boolchand, et al. - "Onset of Rigidity in Steps in Chalcogenide Glasses" Properties and Applications of Amorphous Materials, pgs. 118-124.	

Examiner Signature		Date Considered	4/13/04
--------------------	--	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

RECEIVED
APR 13 2002
Technology Center 2100



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

8

Complete If Known

Application Number	10/075,390
Filing Date	February 15, 2002
First Named Inventor	Kristy A. Campbell
Art Unit	2818
Examiner Name	Not Yet Assigned

Attorney Docket Number M4065.0505/P505

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
KZ	AA	6,388,324	05/14/2002	Kozicki et al.	
KZ	AB	US 2002/0000666	01/03/2002	Kozicki et al.	
KZ	AC	5,500,532	03/19/1996	Kozicki et al.	
KZ	AD	6,418,049	07/09/2002	Kozicki et al.	
KZ	AE	5,751,012	05/12/1998	Wolstenholme et al.	
KZ	AF	5,789,277	08/04/1998	Zahorik et al.	
KZ	AG	6,348,365	02/19/2002	Moore et al.	
AH					
AI					
AJ					
AK					
AL					
AM					
AN					
AO					

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
KZ	BA	WO 02/21542	03/14/2002	Kozicki et al.		
KZ	BB	WO 00/48196	08/17/2000	Kozicki et al.		
KZ	BC	WO 97/48032	12/18/1997	Kozicki et al.		
KZ	BD	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature	<i>M. Campbell</i>	Date Considered	4/13/04
--------------------	--------------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹Applicant's unique citation designation number (optional). ²See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.



Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

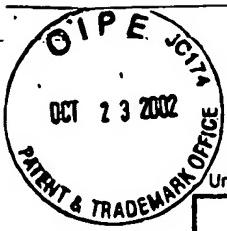
(use as many sheets as necessary)

Sheet	2	of	8	Attorney Docket Number	M4065.0505/P505
-------	---	----	---	------------------------	-----------------

Complete If Known

Application Number	10/075,390
Filing Date	February 15, 2002
First Named Inventor	Kristy A. Campbell
Group Art Unit	2818
Examiner Name	Not Yet Assigned

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MDL	CA	Abdel-All, A.; Elshafie,A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.
JPM	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.
JPM	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.
JPM	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.
JPM	CE	Afifi,M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe1-x, Egypt, J. Phys. 17 (1986) 335-342.
JPM	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.
JPM	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.
JPM	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.
JPM	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.
JPM	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.
JPM	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810
JPM	CL	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.
JPM	CM	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.
JPM	CN	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag7GeSe5I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.
JPM	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.
JPM	CP	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag2Se-M, Thin solid films 70 (1980) L1-L4.
JPM	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.
JPM	CR	Bernede, J.C., Switching and silver movements in Ag2Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.
JPM	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.
JPM	CT	Bernede, J.C.; Conan, A.; Fousenant, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag2Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.
JPM	CU	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al2O3-Ag2-xSe1+x thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.
JPM	CV	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.
JPM	CW	Boolchand, P., The maximum in glass transition temperature (Tg) near x=1/3 in GexSe1-x



PTO/SB/08B (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	3	of	8	Attorney Docket Number	M4065.0505/P505
-------	---	----	---	------------------------	-----------------

		Complaint Known						
		Application Number	10/075,390					
		Filing Date	February 15, 2002					
		First Named Inventor	Kristy A. Campbell					
		Group Art Unit	2818					
		Examiner Name	Not Yet Assigned					
101	CX	Glasses, Asian Journal of Physics (2000) 9, 709-72. Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.						
102	CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703						
103	CZ	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.						
104	CA1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.						
105	CB1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978.						
106	CC1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe1-x glasses, Solid state comm. 45 (1983) 183-185.						
107	CD1	Boolchand, P., Bresser, W.J., Compositional trends in glass transition temperature (Tg), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.						
108	CE1	Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe2 and GeS2 glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 th (1985) 833-36.						
109	CF1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.						
110	CG1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.						
111	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe2 glass, Hyperfine Interactions 27 (1986) 389-392.						
112	CI1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe2 Crystals, Science 258 (1992) 271-274.						
113	CJ1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.						
114	CK1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.						
115	CL1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.						
116	CM1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.						
117	CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.						
118	CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.						
119	CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.						
120	CQ1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.						
121	CR1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.						
122	CS1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.						
123	CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.						
124	CU1	Drusdau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous						



OCT 23 2002

PTO/SB/08B (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE
Subject to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Substitute for form 1449B/PTO				Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/075,390
(use as many sheets as necessary)				Filing Date	February 15, 2002
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	4	of	8	Attorney Docket Number	M4065.0505/P505

		silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
✓	CV1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag _{2-x} Se _{1+x} /n-Si diodes, Thin Solid Films 110 (1983) 107-113.
✓	CW1	El Gharris, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous Ge _x Se _{1-x} photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.
✓	CX1	El Gh randi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.
✓	CY1	El Gh randi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe5.5 thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.
✓	CZ1	El-kady, Y.L., The threshold switching in semiconducting glass Ge ₂₁ Se ₁₇ Te ₆₂ , Indian J. Phys. 70A (1996) 507-516.
✓	CA2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.
✓	CB2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.
✓	CC2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.
✓	CD2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge ₂₀ BixSe _{80-x} films, Thin Solid Films 376 (2000) 236-240.
✓	CE2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.
✓	CF2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se ₇₅ Ge ₇ Sb ₁₈ , Vacuum 43 (1992) 253-257.
✓	CG2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.
✓	CH2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.
✓	CI2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe ₂ thin films, Phys. Rev. B 38 (1988) 12388-12403.
✓	CJ2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.
✓	CK2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.
✓	CL2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.
✓	CM2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag ₂ Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.
✓	CN2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.
✓	CO2	Guin, J.-P.; Rouxel, T.; Kervyn, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below Tg: Plastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.
✓	CP2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.
✓	CQ2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-Cryst. Sol. 3 (1970) 148-154.



PTO/SB/08B (10-01)

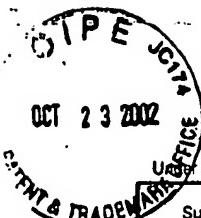
Approved for use through 10/31/2002 OMB 0651-0031

U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		C omplete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>			
Application Number	10/075,390		
Filing Date	February 15, 2002		
First Named Inventor	Kristy A. Campbell		
Group Art Unit	2818		
Examiner Name	Not Yet Assigned		
Sheet	5	of	8
		Attorney Docket Number	
		M4065.0505/P505	

✓	CR2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, <i>J. Non-Cryst. Solids</i> 8-10 (1972) 408-414.
✓	CS2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, <i>J. Appl. Phys.</i> 54 (1983) 1950-1954.
✓	CT2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, <i>Int. J. Electronics</i> 73 (1992) 911-913.
✓	CU2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, <i>J. Non-Cryst. Solids</i> 266-269 (2000) 1058-1061.
✓	CV2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, <i>J. Non-Cryst. Solids</i> 198-200 (1996) 825-828.
✓	CW2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, <i>Phil. Mag. B</i> 63 (1991) 349-369.
✓	CX2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, <i>Japan. J. Appl. Phys.</i> 13 (1974) 1163-1164.
✓	CY2	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, <i>Vacuum</i> 45 (1994) 459-462.
✓	CZ2	Hirose, Y.; Hirose, H., Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As ₂ S ₃ films, <i>J. Appl. Phys.</i> 47 (1976) 2767-2772.
✓	CA3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V ₂ amorphous semiconductor systems, <i>J. Non-Cryst. Solids</i> 116 (1990) 191-200.
✓	CB3	Hosokawa, S., Atomic and electronic structures of glassy Ge _x Se _{1-x} around the stiffness threshold composition, <i>J. Optoelectronics and Advanced Materials</i> 3 (2001) 199-214.
✓	CC3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-Si:H/V thin film devices, <i>J. Non-Cryst. Solids</i> 227-230 (1998) 1187-1191.
✓	CD3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, <i>Phil. Mag. B</i> 74 (1996) 37-50.
✓	CE3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, <i>Phil. Mag. B</i> 80 (2000) 29-43.
✓	CF3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, <i>Solid State Comm.</i> 8 (1970) 153-155.
✓	CG3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge ₂ S ₃ , <i>J. Non-Cryst. Solids</i> 35 & 36 (1980) 1061-1066.
✓	CH3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, <i>J. Non-Cryst. Solids</i> 262 (2000) 135-142.
✓	CI3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, <i>Thin Solid Films</i> 40 (1977) L15-L18.
✓	CJ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As ₂ Se ₇ before switching, <i>Phys. Stat. Sol. (a)</i> 13 (1972) K105-K109.
✓	CK3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As ₂ Se ₅ , <i>Mat. Res. Bull.</i> 8 (1973) 433-442.
✓	CL3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, <i>J. Non-Cryst. Solids</i> 8-10 (1972) 538-543.
✓	CM3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, <i>J. Appl. Phys.</i> 79 (1996) 9096-9104.
✓	CN3	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag ph doping in chalcogenide film, <i>Japan. J. Appl. Phys.</i> 26 (1987) 15-21.



OCT 23 2012

PTO/SB/08B (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

~~Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.~~

Substitute for form 1449B/PTO				Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/075,390
(use as many sheets as necessary)				Filing Date	February 15, 2002
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	6	of	8	Attorney Docket Number	M4065.0505/P505

NR	CO3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Agx(GeSe3)1-x (0<=x<=0.571) glasses, Solid state Ionics 123 (1999) 259-269.
NR	CP3	Kluge, G.; Thomas, A.; Klubes, R.; Grotzschel, R., Silver photodiffusion in amorphous GeSe100-x, J. Non-Cryst. Solids 124 (1990) 186-193.
NR	CQ3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.
NR	CR3	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films, J. Non-Cryst. Solids 137-138 (1991) 1027-1030.
NR	CS3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.
NR	CT3	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTi chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.
NR	CU3	Lakshminarayan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.
NR	CV3	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.
NR	CW3	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.
NR	CX3	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GeSe1-x glass, Appl. Phys. Lett. 46 (1985) 543-545.
NR	CY3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO2 system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.
NR	CZ3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.
NR	CA4	Mazurier, F.; Levy, M.; Souquet, J.L., Reversible and irreversible electrical switching in TeO2-V2O5 based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.
NR	CB4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni,Bi), Mat. Chem. And Phys. 28 (1991) 253-258.
NR	CC4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.
NR	CD4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.
NR	CE4	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.
NR	CF4	Miyatani, S.-y., Electronic and ionic conduction in (AgxCu1-x)2Se, J. Phys. Soc. Japan 34 (1973) 423-432.
NR	CG4	Miyatani, S.-y., Electrical properties of Ag2Se, J. Phys. Soc. Japan 13 (1958) 317.
NR	CH4	Miyatani, S.-y., Ionic conduction in beta-Ag2Te and beta-Ag2Se, Journal Phys. Soc. Japan 14 (1959) 996-1002.
NR	CI4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.
NR	CJ4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.
NR	CK4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glass s, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.
NR	CL4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GexSe1-x amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.
NR	CM4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.



Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	7	of	8	Attorney Docket Number
				M4065.0505/P505

		Complete If Known		
		Application Number	Filing Date	First Named Inventor
	CN4	10/075,390	February 15, 2002	Kristy A. Campbell
	CO4			Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.
	CP4			Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.
	CQ4			Owen, A.E.; LeComber, P.G.; Sarrabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54
	CR4			Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.
	CS4			Owen, A.E.; Le Comber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.
	CT4			Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.
	CU4			Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.
	CV4			Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.
	CW4			Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.
	CX4			Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.
	CY4			Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.
	CZ4			Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.
	CA5			Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.
	CB5			Rose, M.J.; Hajto, J.; Lecomber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.
	CC5			Rose, M.J.; Snell, A.J.; Lecomber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a-Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.
	CD5			Schuocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J. Non-Cryst. Solids 29 (1978) 397-407.
	CE5			Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.
	CF5			Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.
	CG5			Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.
	CH5			Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, L.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.
	CI5			Steventon, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.
	CJ5			Steventon, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.
↓	CK5			Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.



PTO/SB/08B (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

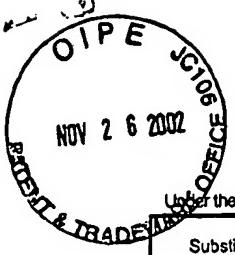
Substitute for form 1449B/PTO				Complete If Known	
				Application Number	10/075,390
				Filing Date	February 15, 2002
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	8	of	8	Attorney Docket Number	M4065.0505/P505

NOV	CL5	Tanaka, K., Ionic and mixed conduction in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.
1	CM5	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.
	CN5	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.
	CO5	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.
	CP5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612.
	CQ5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in Ge _x Se _{1-x} and As _x Se _{1-x} systems, J. Non-Cryst. Solids 261 (2000) 277-281.
	CR5	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.
	CS5	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. 9-13 September 1985.
	CT5	Tregouet, Y.; Bernede, J.C., Silver movements in Ag ₂ Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.
	CU5	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge _{0.4} Se _{0.6} , J. Non-Cryst. Solids 117-118 (1990) 219-221.
	CV5	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.
	CD5	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.
	CX5	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-M system, Mat. Chem. And Phys. 21 (1989) 447-454.
	CY5	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.
	CZ5	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.
	CA6	West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag As _{0.24} S _{0.36} Ag _{0.40} Ag System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974.
	CB6	West, W.C., Electrically erasable non-volatile memory via electrochemical deposition of multi-fractal aggregates, Ph.D. Dissertation, ASU 1998
	CC6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T _g , with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope dT _g /d<m> at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.

Examiner Signature	<i>MSA</i>	Date Considered	4/13/04
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

				Complete if Known		
				Application Number	10/075,390	
				Filing Date	February 15, 2002	
				First Named Inventor	Kristy A. Campbell	
				Art Unit	2818	
				Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number		M4065.0505/P505

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
KX	AA	6,469,364 B1	10/22/2002	Kozicki	
DTL	AB	US2002/0168820 A1	11/14/2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ⁴ -Number ⁵ -Kind Code ⁶ (if known)				

*Applicant's unique citation designation number (optional). ¹See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ²Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ³For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁴Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁵Applicant is to place a check mark here if English language Translation is attached.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.			

Examiner Signature	<i>MFZ</i>	Date Considered	4/13/04
--------------------	------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

RECEIVED
NOV 29 2002
TC 2800 MAIL ROOM



Substitute for form 1449A/PTO

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE
Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet	1	of	4	Attorney Docket Number	M4065.0505/P505
-------	---	----	---	------------------------	-----------------

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
MM	AA	2000/0072188 App	6/2002	Gilton	
MM	AB	2002/0123169 App	9/2002	Moore et al.	
MM	AC	2002/0123248 App.	9/2002	Moore et al.	
NDR	AD	3,622,319	11/1971	Sharp	
NDR	AE	3,743,847	7/1973	Boland	
NDR	AF	4,269,935	5/1981	Masters et al.	
NDR	AG	4,312,938	1/1982	Drexler, et al.	
NDR	AH	4,316,946	1/1982	Masters, et al.	
NDR	AI	4,320,191	3/1982	Yoshikawa et al.	
NDR	AJ	4,405,710	9/1983	Balasubramanyam et al.	
NDR	AK	4,419,421	12/1983	Wichelhaus, et al.	
NDR	AL	4,795,657	1/1989	Formigoni et al.	
NDR	AM	4,847,674	7/1989	Siwa et al.	
NDR	AN	4,499,557	2/1985	Holmberg et al.	
NDR	AO	5,177,567	1/1993	Klersy et al.	
NDR	AP	5,219,788	6/1993	Abermathey et al.	
NDR	AQ	5,238,862	8/1993	Blalock et al.	
NDR	AR	5,315,131	5/1994	Kishimoto et al.	
NDR	AS	5,350,484	9/1994	Gardner et al.	
NDR	AT	5,360,981	11/1994	Owen et al.	
EDN	AU	5,512,328	4/1996	Yoshimura et al.	
EDN	AV	5,512,773	4/1996	Wolf et al.	
NDR	AW	5,726,083	3/1998	Takalshi	
NDR	AX	5,841,150	11/1998	Gonzalez et al.	
NDR	AY	5,846,889	12/1998	Harbison et al.	
NDR	AA1	5,920,788	7/1999	Reinberg	
NDR	AB1	5,998,066	12/1999	Block et al.	
NDR	AC1	6,077,729	6/2000	Harshfield	
NDR	AD1	6,117,720	9/2000	Harshfield	
NDR	AE1	6,143,604	11/2000	Chiang et al.	
NDR	AF1	6,177,338	1/2001	Liaw et al.	
NDR	AG1	6,236,059	5/2001	Wolstenholme et al.	
NDR	AH1	6,297,170	10/2001	Gabriel et al.	
NDR	AI1	6,300,684	10/2001	Gonzalez et al.	
NDR	AJ1	6,316,784	11/2001	Zahorik et al.	
NDR	AK1	6,329,606	12/2001	Freyman et al.	
NDR	AL1	6,350,679	2/2002	McDaniel et al.	
NDR	AM1	6,376,284	4/2002	Gonzalez et al.	
NDR	AN1	6,391,688	5/2002	Gonzalez et al.	
NDR	AO1	6,414,376	7/2002	Thakur et al.	
NDR	AP1	6,423,628	7/2002	Li et al.	
NDR	AQ1	6,487,106	11/26/2002	Kozicki	
NDR	AR1	5,314,772	5/24/1994	Kozicki	
NN	AS1	2002/0190350 APP	12/19/2002	Kozicki	
NN	AT1	2003/0027416 APP	2/6/2003	Moore	



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

Complete If Known

				Application Number	10/075,390
				Filing Date	February 15, 2002
				First Named Inventor	Kristy A. Campbell
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	2	of	4	Attorney Docket Number	M4065.0505/P505

NR	AU1	2003/0001229 APP	1/2/2003	Moore et al.	
NR	AV1	2002/0106849 APP	8/8/2002	Moore	
NR	AW1	2002/0127886 APP	9/12/2002	Moore et al.	
NR	AX1	2002/0123170 APP	9/5/2002	Moore et al.	
NR	AY1	2002/0163828 APP	11/2/2002	Krieger et al.	
NR	AZ1	6,072,716	6/2000	Jacobson et al.	
NR	BA1	5,272,359	12/93	Nagasubramanian et al.	
NR	BB1	4,671,618	6/87	Wu et al.	
NR	BC1	4,800,526	1/89	Lewis	
NR	BD1	2003/0035314 APP	02/02/2003	Kozicki	
NR	BE1	2003/0035315 APP	02/02/2003	Kozicki	
NR	BF1	6,473,332	04/04/01	Ignatiev et al.	



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031
U. S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

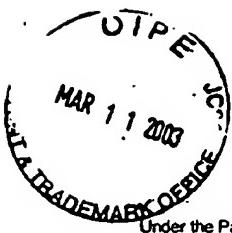
Substitute for form 1449A/PTO				Complete If Known	
				Application Number	10/075,390
				Filing Date	February 15, 2002
				First Named Inventor	Kristy A. Campbell
				Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	3	of	4	Attorney Docket Number	
M4065.0505/P505					

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ² -Number ³ -Kind Code ⁴ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
M	BA	56126916	10/19981	Akira et al.	T ⁵
	BR				

Examiner Signature	<i>MSL/DRB</i>	Date Considered	4/13/04
--------------------	----------------	-----------------	---------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See attached Kind Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

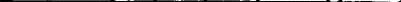


Under the Paperwork Reduction Act of 1985, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

PTO/SB/088 (10-01)

Substitute for form 1449B/PTO				Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/075,390
				Filing Date	July 10, 2002
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818
				Examiner Name	Not Yet Assigned
Sheet	4	of	4	Attorney Docket Number	M4065.0695/P695

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Signature		Date Considered	4/13/04
-----------------------	---	--------------------	---------

***EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

'Applicant's unique citation designation number (optional). **Applicant is to place a check mark here if English language Translation is attached.**